Toshiba Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1044F

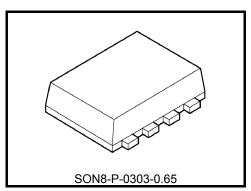
Low-Side Switch for Motor, Solenoid and Lamp Drive

The TPD1044F is a low-side switch.

The IC has a vertical MOSFET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The IC is equipped with intelligent self-protection functions.

Features

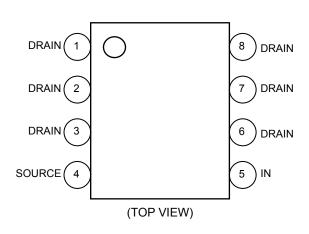
- A monolithic power IC with a new structure combining a control block and a vertical power MOSFET (L^2 - π -MOSV) on single chip.
- Can directly drive a power load from a CMOS or TTL logic.
- Built-in protection circuits against overvoltage (active clamp), overtemperature (thermal shutdown), and overcurrent (current limiter).



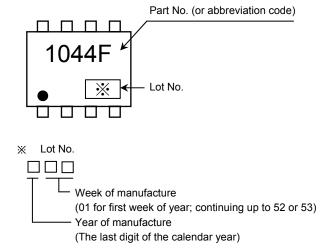
Weight: 0.017 g (typ.)

- Low Drain-Source ON-resistance: RDS (ON) = 0.6Ω (max) (@VIN = 5 V, ID = 0.5 A, Tch = 25°C)
- Low Leakage Current: $IDSS = 10 \mu A (max) (@VIN = 0 V, VDS = 30 V, T_{ch} = 25 °C)$
- Low Input Current: $I_{IN} = 300 \ \mu A (max) (@V_{IN} = 5 \text{ V}, T_{ch} = 25 \text{°C})$
- "PS-8" package with embossed-tape packing.

Pin Assignment (top view)



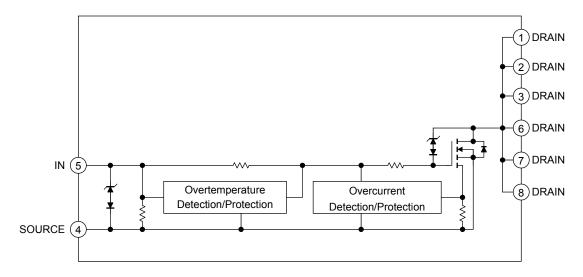
Marking



Note 1: Due to its MOS structure, this product is sensitive to static electricity.

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Block Diagram

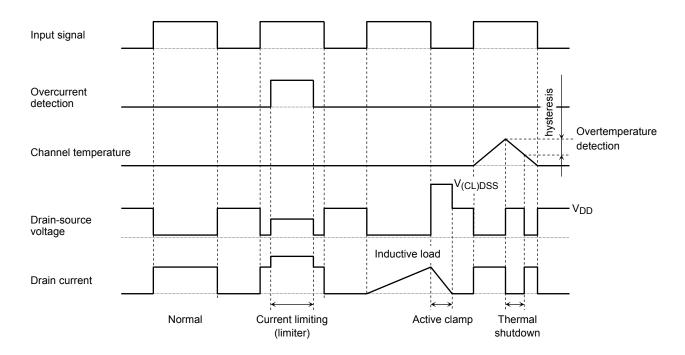


Pin Description

Pin No.	Symbol	Pin Description			
1,2,3,6,7,8	DRAIN	rain current is limited (by current limiter) if it exceeds 1 A (min) in order to protect the IC.			
4	SOURCE	Source pin.			
5	IN	Input pin. This pin is connected to a pull-down resistor internally, so that even when input wiring is open-circuited, output can never be turned on inadvertently.			

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Timing chart



Note 2: The overtemperature detector circuits feature hysteresis. After overtemperature is detected, normal operation is restored only when the channel temperature falls by the hysteresis amount (5°C typ.) in relation to the overtemperature detection temperature.

Truth table

IN	V_{DS}	Output state	Operating state
L	Н	OFF	Normal
Н	L	ON	Nomia
L	Н	OFF	Overcurrent
Н	Н	current limiting(limiter)	(load short)
L	Н	OFF	0
Н	Н	OFF	Overtemperature

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Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V _{DS(DC)}	41	V	
Drain current	I _D	Internally Limited	Α	
Input voltage	V _{IN}	-0.3~7	V	
Power dissipation (Note 3)	PD	0.9	W	
Single pulse active clamp capability (Note 4)	E _{AS}	125	mJ	
Active clamp current	I _{AR}	1	Α	
Repetitive active clamp capability (Note 5)	E _{AR}	0.09	mJ	
Operating temperature	T _{opr}	-40~125	°C	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	−55~150	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to ambient	D.,	138.9	°C/W	
(Note 3)	R _{th (ch-a)}	130.9	C/VV	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

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Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 3:

Drive operation: Mounted on glass epoxy board [25.4mm \times 25.4mm \times 0.8mm]



Note 4: Active clamp capability (single pulse) test condition $V_{DD}=40~V,~T_{ch}=25^{\circ}C(initial),~L=50~mH,~I_{AR}=1~A,~R_{G}=25~\Omega$

Note 5: Repetitive rating, pulse width limited by maximum channel temperature.

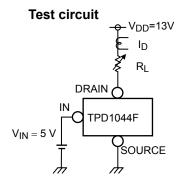
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Electrical Characteristics(Ta = 25°C)

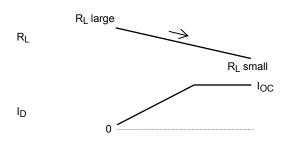
Characteristics	Symbol	Test circuit	Test condition	Min	Тур.	Max	Unit
Drain-source clamp voltage	V _{(CL) DSS}	-	$V_{IN} = 0 \ V, I_D = 1 \ mA$	41	-	60	V
Input threshold voltage	V_{th}	-	$V_{DS} = 13 \text{ V}, I_D = 10 \text{ mA}$	1.0	-	2.8	V
Protective circuit operation input voltage range	V _{IN (opr)}	-	-	3	-	6	V
Drain cut-off current	I _{DSS}	-	V _{IN} = 0 V,V _{DS} = 30 V	-	-	10	μΑ
	I _{IH (1)}	-	V _{IN} = 5 V, at normal operation	-	-	300	μΑ
Input current	l _{IH} (2)	-	V _{IN} = 5 V, when overcurrent protective circuit is actuated	-	-	350	
Drain-source on resistance	R _{DS} (ON)	-	V _{IN} = 5 V, I _D = 0.5 A	-	0.44	0.6	Ω
Overtemperature detection	T _{OT}	-	V _{IN} = 5 V	150	160	-	°C
Overcurrent detection	loc	1	V _{IN} = 5 V	1.0	1.8	-	Α
Switching time	t _{on}	2	$V_{DD} = 13 \text{ V}, V_{IN} = 0 \text{ V/5 V}, I_D = 0.5 \text{ A}$	-	10	-	- μs
	t _{off}			-	15	-	

Test circuit 1

Overcurrent measuring circuit



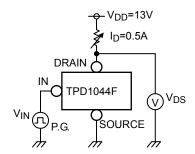
Measured waveforms



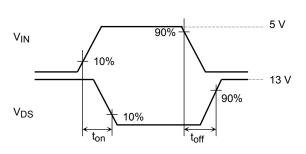
Test circuit 2

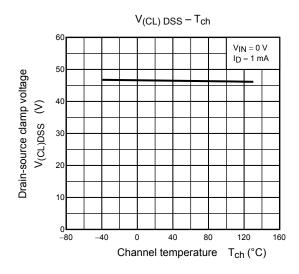
Switching time measuring circuit

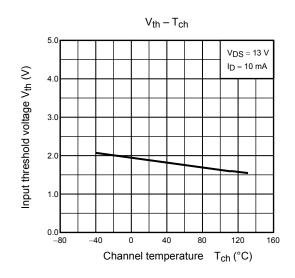
Test circuit

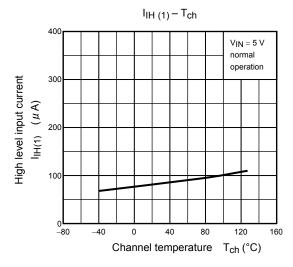


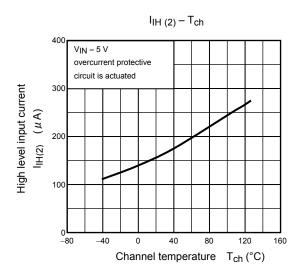
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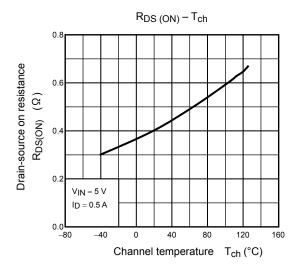


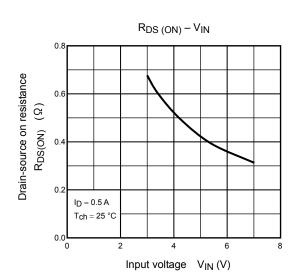




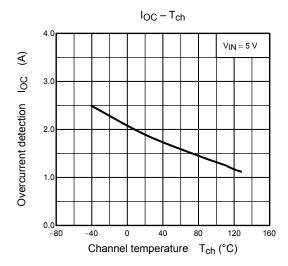


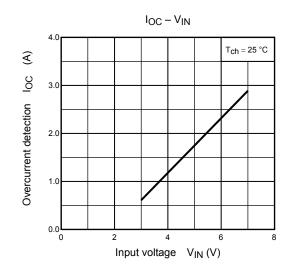


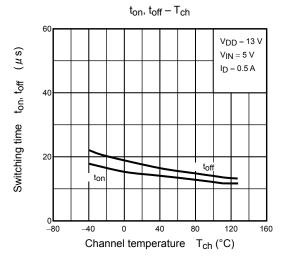


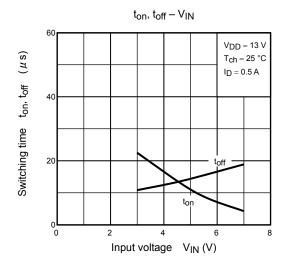


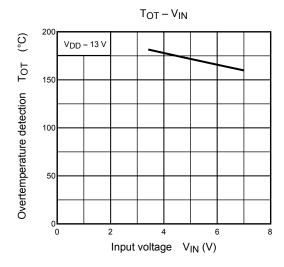
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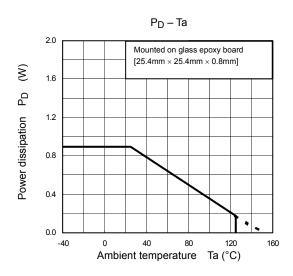


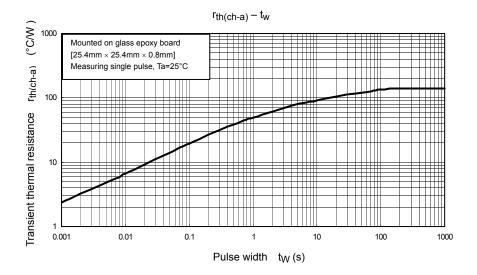






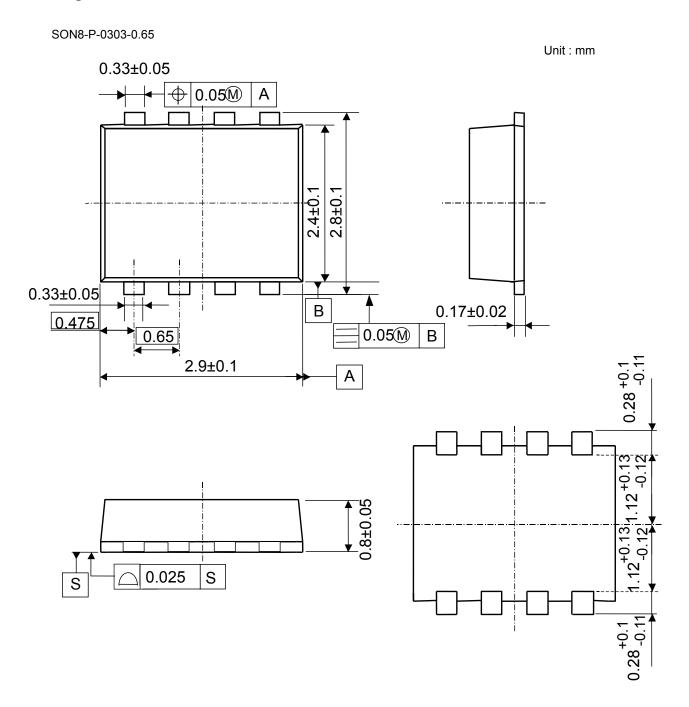






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Package Dimensions



Weight: 0.017 g (Typ.)

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